



SHANGHAI SUNRISE ELECTRONICS CO., LTD.

D10SB10 THRU D10SB100

SINGLE PHASE GLASS

PASSIVATED SIP BRIDGE RECTIFIER

VOLTAGE: 100 TO 1000V CURRENT: 10A

TECHNICAL
SPECIFICATION

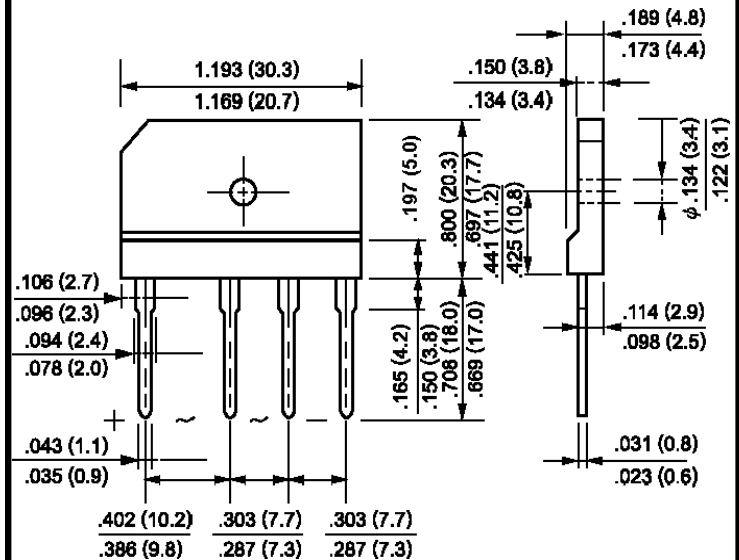
FEATURES

- Glass passivated junction chip
- Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique
- Surge overload rating: 200 A peak
- High temperature soldering guaranteed: 250°C/10sec/ 0.375" (9.5mm) lead length at 5 lbs tension

MECHANICAL DATA

- Terminal: Plated leads solderable per MIL-STD 202E, method 208C
- Case: UL-94 Class V-O recognized flame retardant epoxy
- Polarity: Polarity symbol marked on body
- Mounting position: Any

D10SB



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60Hz, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

RATINGS	SYMBOL	D10SB 10	D10SB 20	D10SB 40	D10SB 60	D10SB 80	D10SB 100	UNITS
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current ($T_a=70^\circ\text{C}$)	$I_{F(AV)}$	10						A
Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load)	I_{FSM}	200						A
Maximum Instantaneous Forward Voltage (at forward current 5.0ADC)	V_F	1.1						V
Maximum DC Reverse Current ($T_a=25^\circ\text{C}$)	I_R	5						μA
(at rated DC blocking voltage) ($T_a=125^\circ\text{C}$)		500						μA
Storage and Operating Junction Temperature	T_{STG}, T_J	-55 to + 150						$^\circ\text{C}$

<http://www.sse-diode.com>